

ABSTRACT

A new method and structure is created for a multi-transistor SRAM device. Standard processing steps are followed for the creation of CMOS devices of providing a patterned layer of gate material, of performing LDD impurity implants, of creating gate spacers. After the creation of the gate spacers, a new step of photoresist patterning and exposure is added. The mask for this additional step is a modified butt-contact mask, comprising enlarging the conventional butt-contact opening by between about 0.005 μm and 0.2 μm , an effect that can also be achieved by photo over-expose. This modified butt-contact mask exposes a spacer that is adjacent to the butt-contact hole, this spacer is removed. S/D impurity implant is performed after which conventional processing steps are applied for completion of the multi-transistor SRAM device.